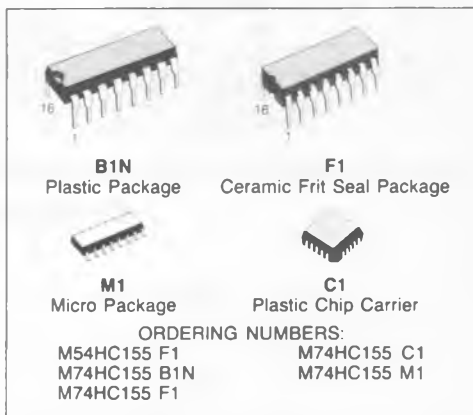


DUAL 2-TO-4 LINE DECODER/3 TO 8 LINE DECODER

- **HIGH SPEED**
 $t_{PD} = 18 \text{ ns (TYP.) at } V_{CC} = 5V$
- **LOW POWER DISSIPATION**
 $I_{CC} = 4 \mu A \text{ (MAX.) at } T_A = 25^\circ C$
- **HIGH NOISE IMMUNITY**
 $V_{NIH} = V_{NIL} = 28\% V_{CC} \text{ (MIN.)}$
- **OUTPUT DRIVE CAPABILITY**
 10 LSTTL LOADS
- **SYMMETRICAL OUTPUT IMPEDANCE**
 $|I_{OH}| = |I_{OL}| = 4 \text{ mA (MIN.)}$
- **BALANCED PROPAGATION DELAYS**
 $t_{PLH} = t_{PHL}$
- **WIDE OPERATING VOLTAGE RANGE**
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 6V$
- **PIN AND FUNCTION COMPATIBLE**
 WITH 54/74LS155



DESCRIPTION

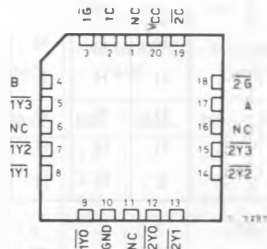
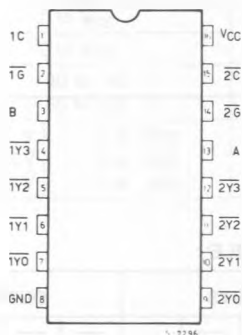
The M54/74HC155 is a high speed CMOS DUAL 2-TO-4 LINE DECODER fabricated in silicon gate CMOS technology.

It has the same high speed performance of LSTTL combined with true CMOS low power consumption. It features dual 1-TO-4 line demultiplexers with individual strobe inputs (1G and 2G), individual data inputs (1C and 2C) and common binary address inputs (A and B).

When both decoders are enabled by the strobes, the inverted output of 1C data and non-inverted output of 2C data will be brought to the select output pins of each sections. A 1-TO-8 line demultiplexer can also be easily built up by providing a data signal to both 1C and 2C inputs; the output order from the msb is 1Y3, 1Y2, 1Y1, 1Y0, 2Y3, 2Y2, 2Y1, 2Y0. This device can be used as a 2-to-4 line decoder or a 3-to-8 line decoder when 1C is held high and 2C is held low.

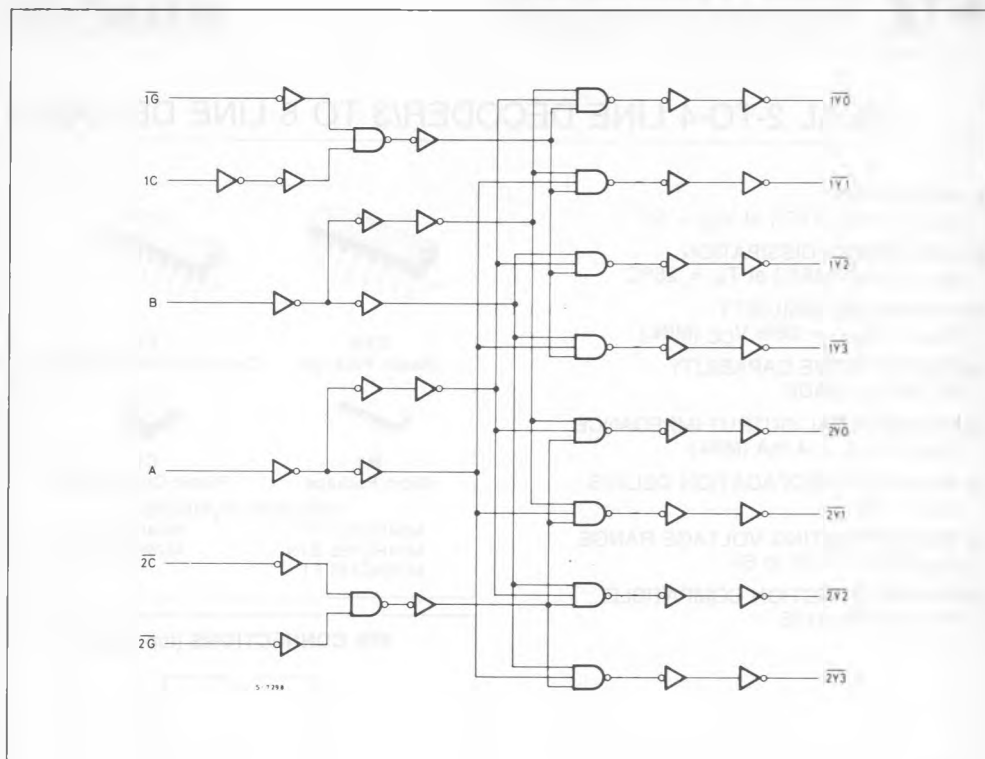
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTIONS (top view)



NC =
No Internal
Connection

LOGIC DIAGRAM



TRUTH TABLE

INPUTS				OUTPUTS			
B	A	1G	1C	1Y0	1Y1	1Y2	1Y3
X	X	H	X	H	H	H	H
L	L	L	H	L	H	H	H
L	H	L	H	H	L	H	H
H	L	L	H	H	H	L	H
H	H	L	H	H	H	H	L
X	X	X	L	H	H	H	H

X: DON'T CARE

INPUTS				OUTPUTS			
B	A	2G	2C	2Y0	2Y1	2Y2	2Y3
X	X	H	X	H	H	H	H
L	L	L	L	L	H	H	H
L	H	L	L	H	L	H	H
H	L	L	L	H	H	L	H
H	H	L	L	H	H	H	L
X	X	X	H	H	H	H	H

X: DON'T CARE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	- 0.5 to 7	V
V_I	DC Input Voltage	- 0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	- 0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	- 65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: $\cong 65^\circ\text{C}$ derate to 300 mW by 10 mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2 to 6	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_A	Operating Temperature 74HC Series 54HC Series	- 40 to 85 - 55 to 125	°C
t_r, t_f	Input Rise and Fall Time	$V_{CC} \begin{cases} 2 \text{ V} & 0 \text{ to } 1000 \\ 4.5 \text{ V} & 0 \text{ to } 500 \\ 6 \text{ V} & 0 \text{ to } 400 \end{cases}$	ns

DC SPECIFICATIONS

Symbol	Parameter	V_{CC}	Test Condition	$T_A = 25^\circ\text{C}$ 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0 4.5 6.0		1.5 3.15 4.2	— — —	— — —	1.5 3.15 4.2	— — —	1.5 3.15 4.2	— — —	V
V_{IL}	Low Level Input Voltage	2.0 4.5 6.0		— — —	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	V

DC SPECIFICATIONS (Continued)

Symbol	Parameter	V _{CC}	Test Condition		T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{OH}	High Level Output Voltage	2.0	V _I	I _O	1.9	2.0	—	1.9	—	1.9	—	V
		4.5	V _{IH} or V _{IL}	- 20 μA	4.4	4.5	—	4.4	—	4.4	—	
		6.0		- 20 μA	5.9	6.0	—	5.9	—	5.9	—	
		4.5	V _{IH} or V _{IL}	- 4.0 mA	4.18	4.31	—	4.13	—	4.10	—	
V _{OL}	Low Level Output Voltage	6.0		- 5.2 mA	5.68	5.8	—	5.63	—	5.60	—	
		2.0	V _{IH} or V _{IL}	20 μA	—	0	0.1	—	0.1	—	0.1	V
		4.5		20 μA	—	0	0.1	—	0.1	—	0.1	
		6.0		20 μA	—	0	0.1	—	0.1	—	0.1	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND	4.0 mA	—	0.17	0.26	—	0.33	—	0.40	μA
				5.2 mA	—	0.18	0.26	—	0.33	—	0.40	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND		—	—	4	—	40	—	80	μA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V, T_A = 25°C, C_L = 15pF, Input t_r = t_f = 6ns)

Symbol	Parameter	54HC and 74HC			Unit
		Min.	Typ.	Max.	
t _{TLH} t _{THL}	Output Transition Time		4	8	ns
t _{PLH} t _{PHL}	Propagation Delay Time		19	30	ns

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input t_r = t_f = 6ns)

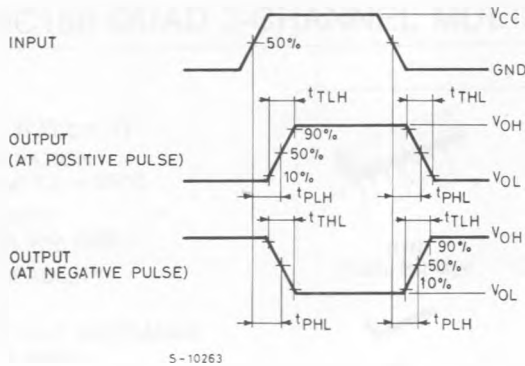
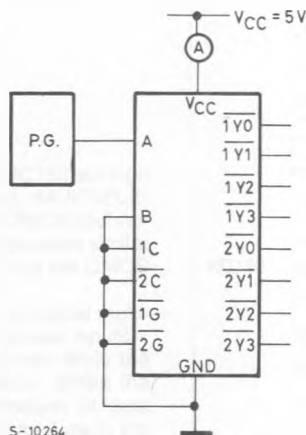
Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			– 40 to 85°C 74HC		– 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} T _{THL}	Output Transition Time	2.0 4.5 6.0		— — —	30 8 7	75 15 13	— — —	95 19 16	— — —	110 22 19	ns
t _{PLH} t _{PHL}	Propagation Delay Time	2.0 4.5 6.0		— — —	88 22 19	175 35 30	— — —	220 44 37	— — —	265 53 45	ns
C _{IN}	Input Capacitance			—	5	10	—	10	—	10	pF
C _{PD} (*)	Power Dissipation Capacitance			—	65	—	—	—	—	—	pF

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load (refer to Test circuit).

Average operating current can be obtained by equation hereunder.

$$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

SWITCHING CHARACTERISTICS TEST WAVEFORM

TEST WAVEFORM I_{CC} (Opr.)

INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST